

trench of oxide

intended to
make trenches

first of
trenches =
pillars
bury pillar in first
step of oxidizing

-5-

ONS00325

10/102,505

IN THE CLAIMS

Please cancel claims 1-28, which were elected in parent application 10/102,505 pursuant to a restriction requirement under 35 U.S.C. § 121 dated May 7, 2003. Add new claims 31-43 as follows. Claims 29-43 are pending in the application.

Please cancel claims 1-28.

29. (Original) A method of making a semiconductor structure, comprising the steps of:

oxidizing sidewalls of cavities in a semiconductor material to form a continuous oxide layer between adjacent cavities; and ^{burying the} ~~burying the~~ ^{of S.C. Material} ~~burying the~~ ^{etching}

etching the continuous oxide layer to ~~leave~~ ^{to form} a pillar of the semiconductor material. ^{to exposing sub}

30. (Original) The method of claim 29, wherein the cavities are formed in a region of the semiconductor material, further comprising the step of depositing a dielectric material over the region to form a void adjacent to the pillar.

31. (New) A method of making a semiconductor structure, comprising:

forming a pillar with a semiconductor material below a surface of a substrate;

capping the pillar with a first dielectric material to form a void; and

forming an electrical component on the dielectric material over the void.

interview w/ Kevin Jackson
Bruce Huling 8/4 1:21 PM

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32. (New) The method of claim 31, wherein the electrical component comprises a passive device or bonding pad.
33. (New) The method of claim 32, wherein the semiconductor material comprises monocrystalline silicon.
34. (New) The method of claim 31, wherein the step of capping the pillar includes the step of coating the pillar with a second dielectric material.
35. (New) The method of claim 34, wherein the second dielectric material comprises thermally grown oxide or silicon nitride.
36. (New) The method of claim 35, wherein the first dielectric material comprises deposited silicon dioxide.
37. (New) The method of claim 31, wherein the void is formed having a depth of at least five micrometers below the surface of the semiconductor material.
38. (New) The method of claim 31, wherein the pillar is formed having a height of at least five micrometers below the surface of the semiconductor material.
39. (New) A method of making a semiconductor device, comprising:
forming a silicon pillar below a surface of a semiconductor substrate;
capping the silicon pillar with a first dielectric material to form a void; and
forming an electrical component over the void.

p. 4, line 33 typo: contiguous? → "

spacing + part step

40. (New) The method of claim 39, wherein the silicon pillar is formed to a height of greater than five micrometers.

41. (New) The method of claim 40, wherein the step of capping the silicon pillar includes the step of coating the silicon pillar with a second dielectric layer.

42. (New) The method of claim 41, wherein the second dielectric material is comprised of deposited silicon dioxide or silicon nitride.

43. (New) The method of claim 39, wherein the electrical component comprises a passive device or bonding pad.